

NX3L4051

Single low-ohmic 8-channel analog switch

Rev. 2 — 12 August 2010

Product data sheet

1. General description

The NX3L4051 is an 8-channel analog switch, suitable for use as an analog or digital multiplexer/demultiplexer. The NX3L4051 has three digital select inputs (S1 to S3), eight independent inputs/outputs (Y0 to Y7) and a common input/output (Z). All eight switches share an enable input (\bar{E}). A HIGH on \bar{E} causes all switches into the high impedance OFF-state, independent of Sn. Schmitt trigger action at the select input (Sn and \bar{E}) makes the circuit tolerant to slower input rise and fall times across the entire V_{CC} range from 1.4 V to 4.3 V.

A low input voltage threshold allows pin Sn and \bar{E} to be driven by lower level logic signals without a significant increase in supply current I_{CC} . This makes it possible for the NX3L4051 to switch 4.3 V signals with a 1.8 V digital controller, eliminating the need for logic level translation. The NX3L4051 allows signals with amplitude up to V_{CC} to be transmitted from Z to Yn or from Yn to Z. Its low ON resistance (0.5 Ω) and flatness (0.13 Ω) ensures minimal attenuation and distortion of transmitted signals.

2. Features and benefits

- Wide supply voltage range from 1.4 V to 4.3 V
- Very low ON resistance (peak):
 - ◆ 1.7 Ω (typical) at $V_{CC} = 1.4$ V
 - ◆ 1.0 Ω (typical) at $V_{CC} = 1.65$ V
 - ◆ 0.6 Ω (typical) at $V_{CC} = 2.3$ V
 - ◆ 0.5 Ω (typical) at $V_{CC} = 2.7$ V
 - ◆ 0.5 Ω (typical) at $V_{CC} = 4.3$ V
- Break-before-make switching
- High noise immunity
- ESD protection:
 - ◆ HBM JESD22-A114F Class 3A exceeds 7500 V
 - ◆ MM JESD22-A115-A exceeds 200 V
 - ◆ CDM AEC-Q100-011 revision B exceeds 1000 V
- CMOS low-power consumption
- Latch-up performance exceeds 100 mA per JESD 78B Class II Level A
- 1.8 V control logic at $V_{CC} = 3.6$ V
- Control input accepts voltages above supply voltage
- Very low supply current, even when input is below V_{CC}
- High current handling capability (350 mA continuous current under 3.3 V supply)
- Specified from -40 °C to $+85$ °C and from -40 °C to $+125$ °C



3. Applications

- Cell phone
- PDA
- Portable media player
- Analog multiplexing and demultiplexing
- Digital multiplexing and demultiplexing
- Signal gating

4. Ordering information

Table 1. Ordering information

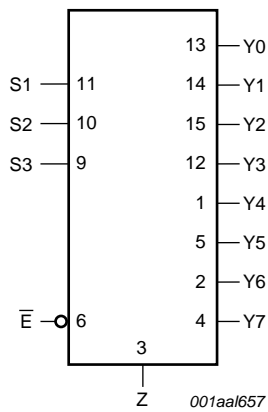
Type number	Package			Version
	Temperature range	Name	Description	
NX3L4051HR	-40 °C to +125 °C	HXQFN16U	plastic thermal enhanced extremely thin quad flat package; no leads; 16 terminals; UTLP based; body 3 × 3 × 0.5 mm	SOT1039-1
NX3L4051PW	-40 °C to +125 °C	TSSOP16	plastic thin shrink small outline package; 16 leads; body width 4.4 mm	SOT403-1

5. Marking

Table 2. Marking codes

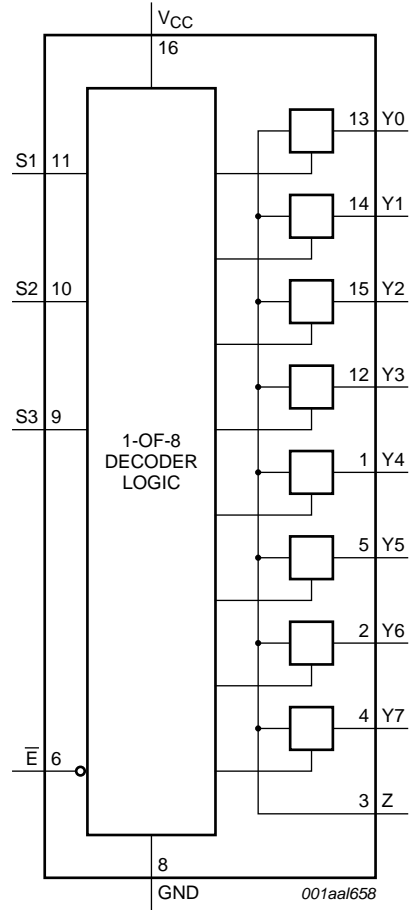
Type number	Marking code
NX3L4051HR	M41
NX3L4051PW	X3L4051

6. Functional diagram



Pin numbers are shown for TSSOP16 package only.

Fig 1. Logic symbol

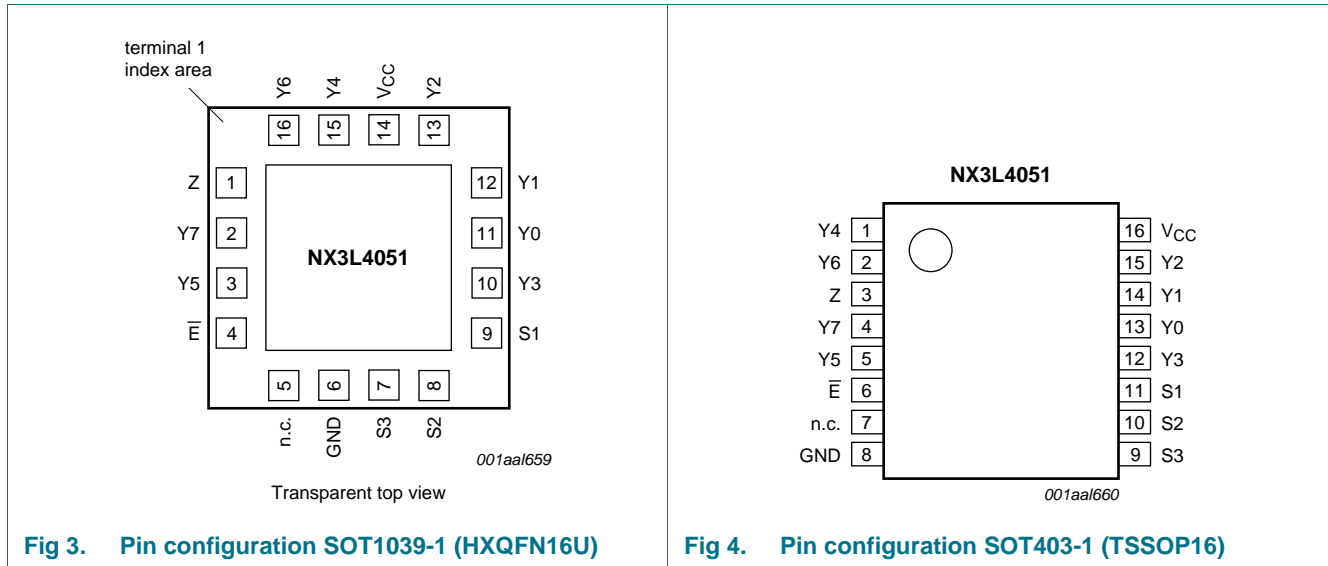


Pin numbers are shown for TSSOP16 package only.

Fig 2. Functional diagram

7. Pinning information

7.1 Pinning



7.2 Pin description

Table 3. Pin description

Symbol	Pin		Description
	SOT1039-1	SOT403-1	
Y0, Y1, Y2, Y3, Y4, Y5, Y6, Y7	11, 12, 13, 10, 15, 3, 16, 2	13, 14, 15, 12, 1, 5, 2, 4	independent input or output
Z	1	3	independent output or input
\bar{E}	4	6	enable input (active LOW)
n.c.	5	7	not connected
GND	6	8	ground (0 V)
S1, S2, S3	9, 8, 7	11, 10, 9	select input
V _{CC}	14	16	supply voltage

8. Functional description

Table 4. Function table^[1]

Input				Channel ON
\bar{E}	S3	S2	S1	
L	L	L	L	Y0 = Z
L	L	L	H	Y1 = Z
L	L	H	L	Y2 = Z
L	L	H	H	Y3 = Z
L	H	L	L	Y4 = Z
L	H	L	H	Y5 = Z
L	H	H	L	Y6 = Z
L	H	H	H	Y7 = Z
H	X	X	X	switches off

[1] H = HIGH voltage level; L = LOW voltage level; X = don't care.

9. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{CC}	supply voltage		-0.5	+4.6	V
V_I	input voltage	S_n and \bar{E}	^[1] -0.5	+4.6	V
V_{SW}	switch voltage		^[2] -0.5	$V_{CC} + 0.5$	V
I_{IK}	input clamping current	$V_I < -0.5$ V	-50	-	mA
I_{SK}	switch clamping current	$V_I < -0.5$ V or $V_I > V_{CC} + 0.5$ V	-	± 50	mA
I_{SW}	switch current	$V_{SW} > -0.5$ V or $V_{SW} < V_{CC} + 0.5$ V; source or sink current	-	± 350	mA
		$V_{SW} > -0.5$ V or $V_{SW} < V_{CC} + 0.5$ V; pulsed at 1 ms duration, < 10 % duty cycle; peak current	-	± 500	mA
T_{stg}	storage temperature		-65	+150	°C
P_{tot}	total power dissipation	$T_{amb} = -40$ °C to +125 °C			
		HXQFN16U	^[3] -	250	mW
		TSSOP16	^[4] -	500	mW

[1] The minimum input voltage rating may be exceeded if the input current rating is observed.

[2] The minimum and maximum switch voltage ratings may be exceeded if the switch clamping current rating is observed but may not exceed 4.6 V.

[3] For HXQFN16U package: above 135 °C the value of P_{tot} derates linearly with 16.9 mW/K.

[4] For TSSOP16 package: above 60 °C the value of P_{tot} derates linearly with 5.5 mW/K above.

10. Recommended operating conditions

Table 6. Recommended operating conditions

Symbol	Parameter	Conditions	Min	Max	Unit
V_{CC}	supply voltage		1.4	4.3	V
V_I	input voltage	Sn and \bar{E}	0	4.3	V
V_{SW}	switch voltage		[1] 0	V_{CC}	V
T_{amb}	ambient temperature		-40	+125	°C
$\Delta t/\Delta V$	input transition rise and fall rate	Sn and \bar{E} ; $V_{CC} = 1.4\text{ V to }4.3\text{ V}$	-	200	ns/V

[1] To avoid sinking GND current from terminal Z when switch current flows in terminal Yn, the voltage drop across the bidirectional switch must not exceed 0.4 V. If the switch current flows into terminal Z, no GND current will flow from terminal Yn. In this case, there is no limit for the voltage drop across the switch.

11. Static characteristics

Table 7. Static characteristics

At recommended operating conditions; voltages are referenced to GND (ground 0 V).

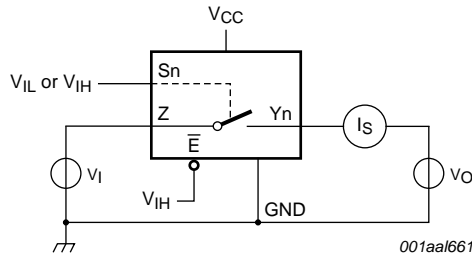
Symbol	Parameter	Conditions	$T_{amb} = 25\text{ °C}$			$T_{amb} = -40\text{ °C to }+125\text{ °C}$			Unit
			Min	Typ	Max	Min	Max (85 °C)	Max (125 °C)	
V_{IH}	HIGH-level input voltage	$V_{CC} = 1.4\text{ V to }1.6\text{ V}$	0.9	-	-	0.9	-	-	V
		$V_{CC} = 1.65\text{ V to }1.95\text{ V}$	0.9	-	-	0.9	-	-	V
		$V_{CC} = 2.3\text{ V to }2.7\text{ V}$	1.1	-	-	1.1	-	-	V
		$V_{CC} = 2.7\text{ V to }3.6\text{ V}$	1.3	-	-	1.3	-	-	V
		$V_{CC} = 3.6\text{ V to }4.3\text{ V}$	1.4	-	-	1.4	-	-	V
V_{IL}	LOW-level input voltage	$V_{CC} = 1.4\text{ V to }1.6\text{ V}$	-	-	0.3	-	0.3	0.3	V
		$V_{CC} = 1.65\text{ V to }1.95\text{ V}$	-	-	0.4	-	0.4	0.3	V
		$V_{CC} = 2.3\text{ V to }2.7\text{ V}$	-	-	0.4	-	0.4	0.4	V
		$V_{CC} = 2.7\text{ V to }3.6\text{ V}$	-	-	0.5	-	0.5	0.5	V
		$V_{CC} = 3.6\text{ V to }4.3\text{ V}$	-	-	0.6	-	0.6	0.6	V
I_I	input leakage current	Sn and \bar{E} ; $V_I = \text{GND to }4.3\text{ V}$; $V_{CC} = 1.4\text{ V to }4.3\text{ V}$	-	-	-	-	± 0.5	± 1	μA
$I_{S(OFF)}$	OFF-state leakage current	Yn ports; see Figure 5							
		$V_{CC} = 1.4\text{ V to }3.6\text{ V}$	-	-	± 5	-	± 50	± 500	nA
		$V_{CC} = 3.6\text{ V to }4.3\text{ V}$	-	-	± 10	-	± 50	± 500	nA
$I_{S(ON)}$	ON-state leakage current	Z port; $V_{CC} = 1.4\text{ V to }3.6\text{ V}$; see Figure 6							
		$V_{CC} = 1.4\text{ V to }3.6\text{ V}$	-	-	± 20	-	± 200	± 2000	nA
		$V_{CC} = 3.6\text{ V to }4.3\text{ V}$	-	-	± 40	-	± 200	± 2000	nA
I_{CC}	supply current	$V_I = V_{CC}\text{ or GND}$; $V_{SW} = \text{GND or }V_{CC}$							
		$V_{CC} = 3.6\text{ V}$	-	-	100	-	500	5000	nA
		$V_{CC} = 4.3\text{ V}$	-	-	150	-	800	6000	nA

Table 7. Static characteristics ...continued

At recommended operating conditions; voltages are referenced to GND (ground 0 V).

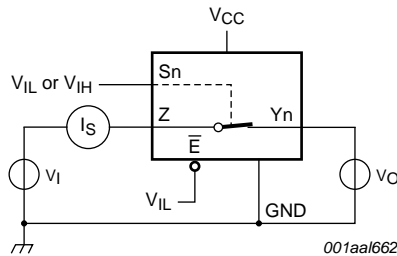
Symbol	Parameter	Conditions	T _{amb} = 25 °C			T _{amb} = -40 °C to +125 °C			Unit
			Min	Typ	Max	Min	Max (85 °C)	Max (125 °C)	
ΔI _{CC}	additional supply current	V _{SW} = GND or V _{CC}							
		V _I = 2.6 V; V _{CC} = 4.3 V	-	2.0	4.0	-	7	7	μA
		V _I = 2.6 V; V _{CC} = 3.6 V	-	0.35	0.7	-	1	1	μA
		V _I = 1.8 V; V _{CC} = 4.3 V	-	7.0	10.0	-	15	15	μA
		V _I = 1.8 V; V _{CC} = 3.6 V	-	2.5	4.0	-	5	5	μA
		V _I = 1.8 V; V _{CC} = 2.5 V	-	50	200	-	300	500	nA
C _I	input capacitance	Sn and \bar{E}	-	1.0	-	-	-	-	pF
C _{S(OFF)}	OFF-state capacitance		-	35	-	-	-	-	pF
C _{S(ON)}	ON-state capacitance		-	350	-	-	-	-	pF

11.1 Test circuits



V_I = 0.3 V or V_{CC} - 0.3 V; V_O = V_{CC} - 0.3 V or 0.3 V.

Fig 5. Test circuit for measuring OFF-state leakage current



V_I = 0.3 V or V_{CC} - 0.3 V; V_O = V_{CC} - 0.3 V or 0.3 V.

Fig 6. Test circuit for measuring ON-state leakage current

11.2 ON resistance

Table 8. ON resistance^[1]

At recommended operating conditions; voltages are referenced to GND (ground = 0 V); for graphs see [Figure 8](#) to [Figure 14](#).

Symbol	Parameter	Conditions	T _{amb} = -40 °C to +85 °C			T _{amb} = -40 °C to +125 °C		Unit
			Min	Typ ^[2]	Max	Min	Max	
R _{ON(peak)}	ON resistance (peak)	V _I = GND to V _{CC} ; I _{SW} = 100 mA; see Figure 7						
		V _{CC} = 1.4 V	-	1.7	3.7	-	4.1	Ω
		V _{CC} = 1.65 V	-	1.0	1.6	-	1.7	Ω
		V _{CC} = 2.3 V	-	0.6	0.8	-	0.9	Ω
		V _{CC} = 2.7 V	-	0.5	0.75	-	0.9	Ω
		V _{CC} = 4.3 V	-	0.5	0.75	-	0.9	Ω
ΔR _{ON}	ON resistance mismatch between channels	V _I = GND to V _{CC} ; I _{SW} = 100 mA [3]						
		V _{CC} = 1.4 V; V _{SW} = 0.4 V	-	0.18	0.30	-	0.30	Ω
		V _{CC} = 1.65 V; V _{SW} = 0.5 V	-	0.18	0.20	-	0.30	Ω
		V _{CC} = 2.3 V; V _{SW} = 0.7 V	-	0.07	0.10	-	0.13	Ω
		V _{CC} = 2.7 V; V _{SW} = 0.8 V	-	0.07	0.10	-	0.13	Ω
		V _{CC} = 4.3 V; V _{SW} = 0.8 V	-	0.07	0.10	-	0.13	Ω
R _{ON(flat)}	ON resistance (flatness)	V _I = GND to V _{CC} ; I _{SW} = 100 mA [4]						
		V _{CC} = 1.4 V	-	1.0	3.3	-	3.6	Ω
		V _{CC} = 1.65 V	-	0.5	1.2	-	1.3	Ω
		V _{CC} = 2.3 V	-	0.15	0.3	-	0.35	Ω
		V _{CC} = 2.7 V	-	0.13	0.3	-	0.35	Ω
		V _{CC} = 4.3 V	-	0.2	0.4	-	0.45	Ω

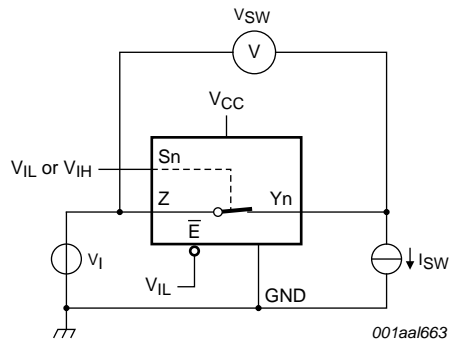
[1] For NX3L4051PW (TSSOP16 package), all ON resistance values are up to 0.05 Ω higher.

[2] Typical values are measured at T_{amb} = 25 °C.

[3] Measured at identical V_{CC}, temperature and input voltage.

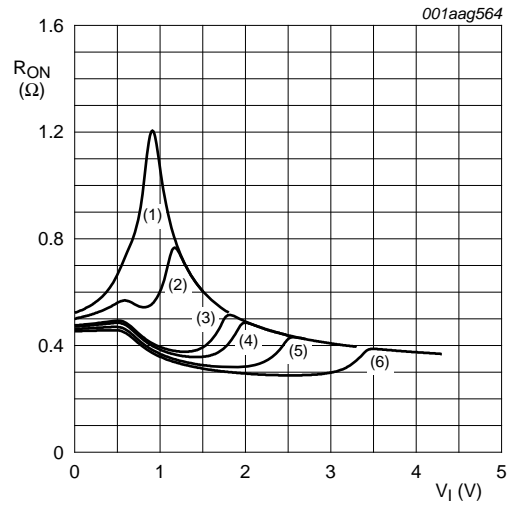
[4] Flatness is defined as the difference between the maximum and minimum value of ON resistance measured at identical V_{CC} and temperature.

11.3 ON resistance test circuit and graphs



$R_{ON} = V_{SW} / I_{SW}$.

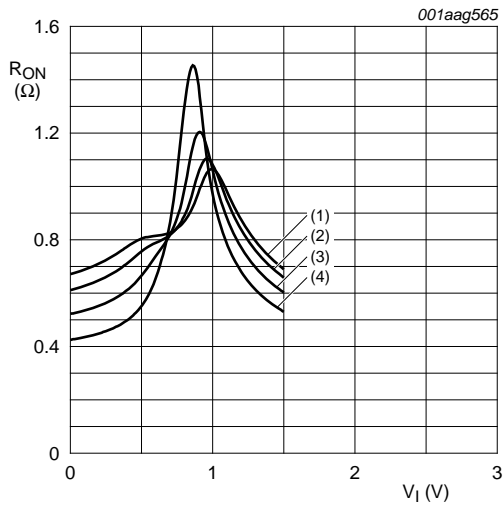
Fig 7. Test circuit for measuring ON resistance



- (1) $V_{CC} = 1.5 \text{ V}$.
- (2) $V_{CC} = 1.8 \text{ V}$.
- (3) $V_{CC} = 2.5 \text{ V}$.
- (4) $V_{CC} = 2.7 \text{ V}$.
- (5) $V_{CC} = 3.3 \text{ V}$.
- (6) $V_{CC} = 4.3 \text{ V}$.

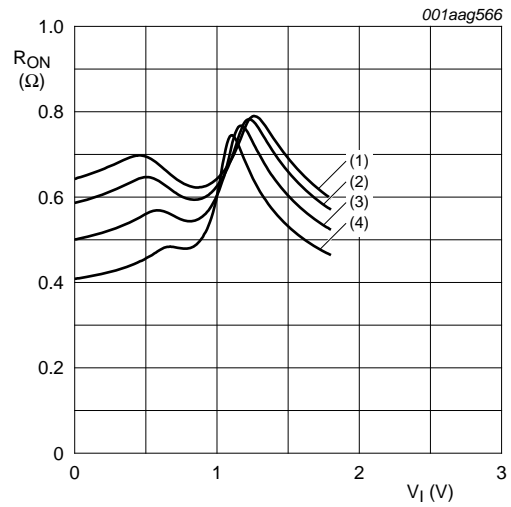
Measured at $T_{amb} = 25 \text{ }^\circ\text{C}$.

Fig 8. Typical ON resistance as a function of input voltage



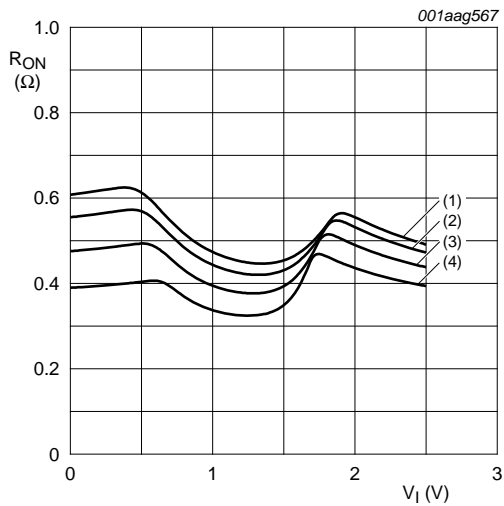
- (1) $T_{amb} = 125\text{ }^{\circ}\text{C}.$
- (2) $T_{amb} = 85\text{ }^{\circ}\text{C}.$
- (3) $T_{amb} = 25\text{ }^{\circ}\text{C}.$
- (4) $T_{amb} = -40\text{ }^{\circ}\text{C}.$

Fig 9. ON resistance as a function of input voltage;
 $V_{CC} = 1.5\text{ V}$



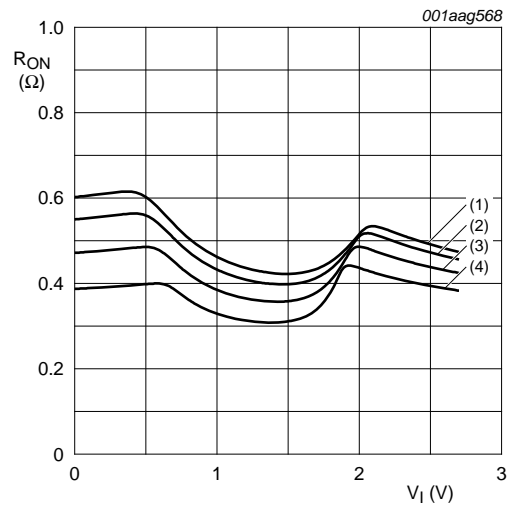
- (1) $T_{amb} = 125\text{ }^{\circ}\text{C}.$
- (2) $T_{amb} = 85\text{ }^{\circ}\text{C}.$
- (3) $T_{amb} = 25\text{ }^{\circ}\text{C}.$
- (4) $T_{amb} = -40\text{ }^{\circ}\text{C}.$

Fig 10. ON resistance as a function of input voltage;
 $V_{CC} = 1.8\text{ V}$



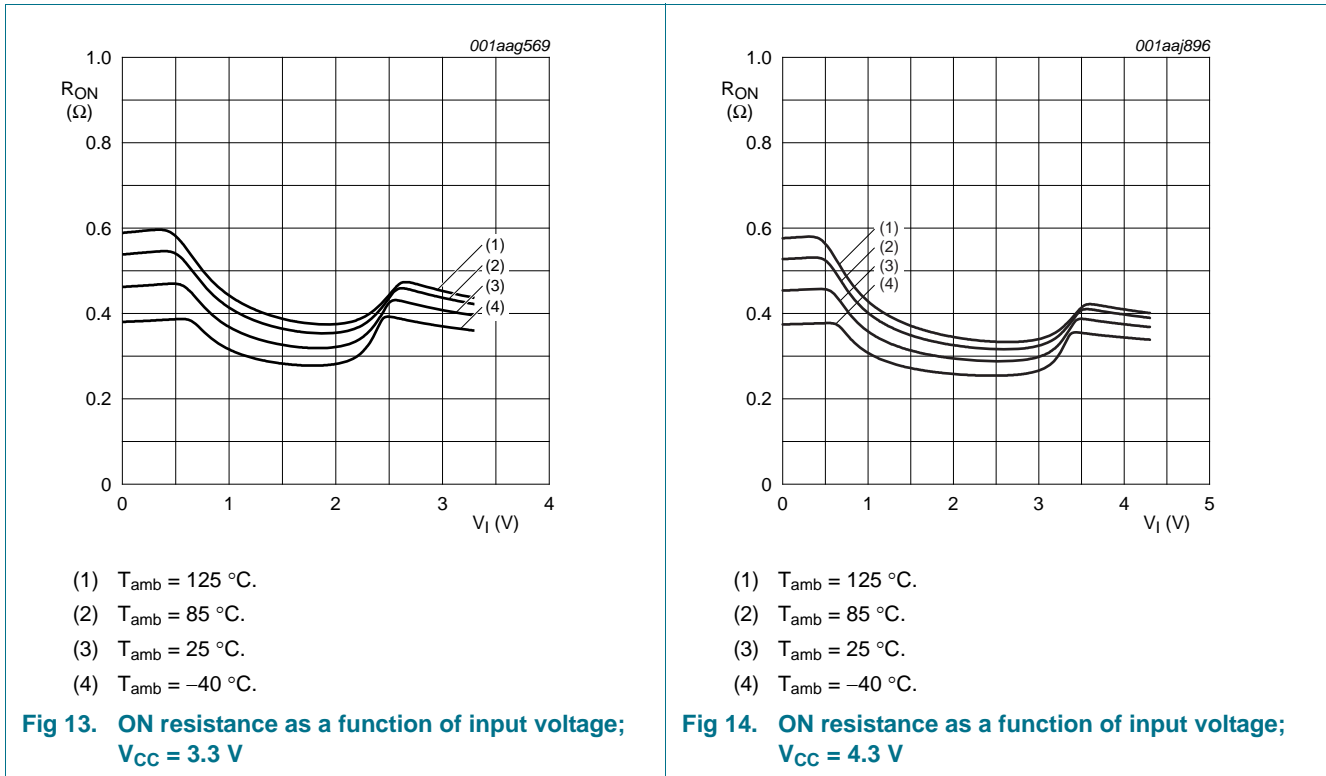
- (1) $T_{amb} = 125\text{ }^{\circ}\text{C}.$
- (2) $T_{amb} = 85\text{ }^{\circ}\text{C}.$
- (3) $T_{amb} = 25\text{ }^{\circ}\text{C}.$
- (4) $T_{amb} = -40\text{ }^{\circ}\text{C}.$

Fig 11. ON resistance as a function of input voltage;
 $V_{CC} = 2.5\text{ V}$



- (1) $T_{amb} = 125\text{ }^{\circ}\text{C}.$
- (2) $T_{amb} = 85\text{ }^{\circ}\text{C}.$
- (3) $T_{amb} = 25\text{ }^{\circ}\text{C}.$
- (4) $T_{amb} = -40\text{ }^{\circ}\text{C}.$

Fig 12. ON resistance as a function of input voltage;
 $V_{CC} = 2.7\text{ V}$



12. Dynamic characteristics

Table 9. Dynamic characteristics

At recommended operating conditions; voltages are referenced to GND (ground = 0 V); for load circuit see [Figure 17](#).

Symbol	Parameter	Conditions	25 °C			-40 °C to +125 °C			Unit
			Min	Typ ^[1]	Max	Min	Max (85 °C)	Max (125 °C)	
t _{en}	enable time	\bar{E} , Sn to Z or Yn; see Figure 15 V _{CC} = 1.4 V to 1.6 V V _{CC} = 1.65 V to 1.95 V V _{CC} = 2.3 V to 2.7 V V _{CC} = 2.7 V to 3.6 V V _{CC} = 3.6 V to 4.3 V	-	45	100	-	120	125	ns
			-	32	75	-	85	95	ns
			-	21	50	-	55	60	ns
			-	19	45	-	45	50	ns
			-	19	45	-	45	50	ns
t _{dis}	disable time	\bar{E} , Sn to Z or Yn; see Figure 15 V _{CC} = 1.4 V to 1.6 V V _{CC} = 1.65 V to 1.95 V V _{CC} = 2.3 V to 2.7 V V _{CC} = 2.7 V to 3.6 V V _{CC} = 3.6 V to 4.3 V	-	25	80	-	90	105	ns
			-	15	65	-	70	75	ns
			-	9	30	-	35	40	ns
			-	8	25	-	30	35	ns
			-	8	25	-	30	35	ns

Table 9. Dynamic characteristics ...continued

At recommended operating conditions; voltages are referenced to GND (ground = 0 V); for load circuit see [Figure 17](#).

Symbol	Parameter	Conditions	25 °C			-40 °C to +125 °C			Unit
			Min	Typ ^[1]	Max	Min	Max (85 °C)	Max (125 °C)	
t_{b-m}	break-before-make time	see Figure 16 ^[2]							
		$V_{CC} = 1.4 \text{ V to } 1.6 \text{ V}$	-	19	-	9	-	-	ns
		$V_{CC} = 1.65 \text{ V to } 1.95 \text{ V}$	-	17	-	7	-	-	ns
		$V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$	-	12	-	4	-	-	ns
		$V_{CC} = 2.7 \text{ V to } 3.6 \text{ V}$	-	10	-	3	-	-	ns
		$V_{CC} = 3.6 \text{ V to } 4.3 \text{ V}$	-	9	-	2	-	-	ns

[1] Typical values are measured at $T_{amb} = 25 \text{ °C}$ and $V_{CC} = 1.5 \text{ V}, 1.8 \text{ V}, 2.5 \text{ V}, 3.3 \text{ V}$ and 4.3 V respectively.

[2] Break-before-make guaranteed by design.

12.1 Waveform and test circuits

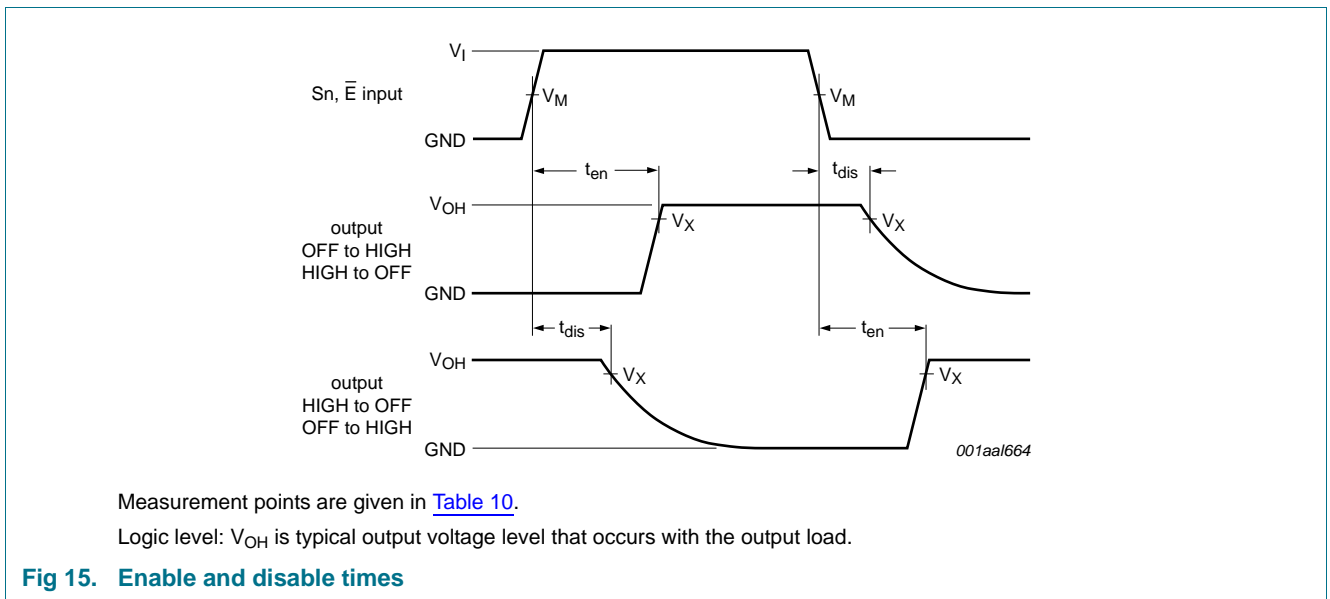


Table 10. Measurement points

Supply voltage	Input	Output
V_{CC}	V_M	V_X
1.4 V to 4.3 V	$0.5V_{CC}$	$0.9V_{OH}$

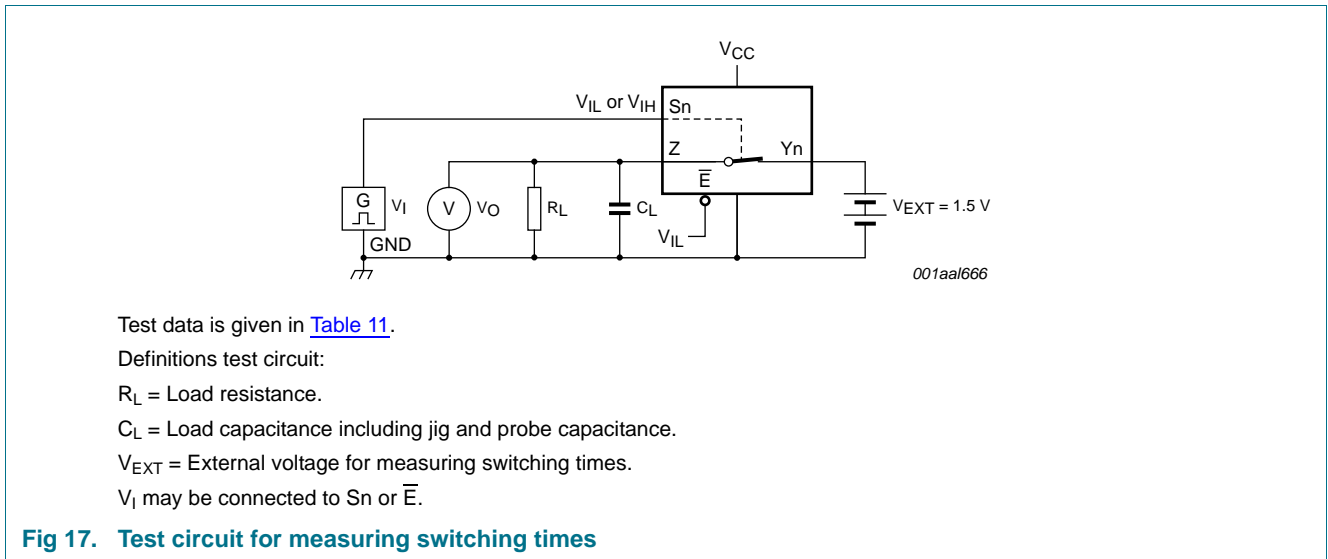
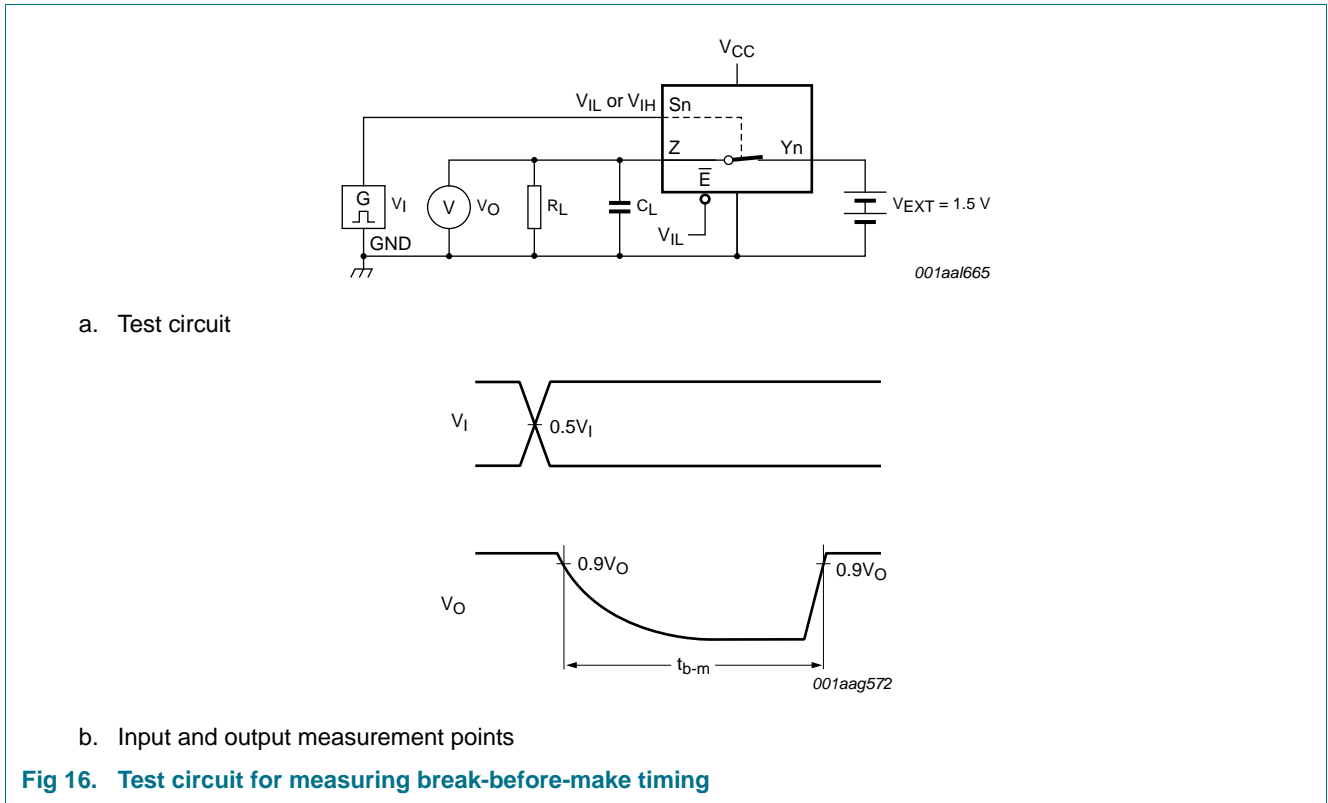


Table 11. Test data

Supply voltage	Input		Load	
V_{CC}	V_I	t_r, t_f	C_L	R_L
1.4 V to 4.3 V	V_{CC}	≤ 2.5 ns	35 pF	50 Ω

12.2 Additional dynamic characteristics

Table 12. Additional dynamic characteristics

At recommended operating conditions; voltages are referenced to GND (ground = 0 V); $V_I = \text{GND}$ or V_{CC} (unless otherwise specified); $t_r = t_f \leq 2.5 \text{ ns}$; $T_{amb} = 25 \text{ }^\circ\text{C}$.

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
THD	total harmonic distortion	$f_i = 20 \text{ Hz to } 20 \text{ kHz}; R_L = 32 \text{ } \Omega$; see Figure 18	[1]			
		$V_{CC} = 1.4 \text{ V}; V_I = 1 \text{ V (p-p)}$	-	0.15	-	%
		$V_{CC} = 1.65 \text{ V}; V_I = 1.2 \text{ V (p-p)}$	-	0.10	-	%
		$V_{CC} = 2.3 \text{ V}; V_I = 1.5 \text{ V (p-p)}$	-	0.02	-	%
		$V_{CC} = 2.7 \text{ V}; V_I = 2 \text{ V (p-p)}$	-	0.02	-	%
		$V_{CC} = 4.3 \text{ V}; V_I = 2 \text{ V (p-p)}$	-	0.02	-	%
$f_{(-3\text{dB})}$	-3 dB frequency response	$R_L = 50 \text{ } \Omega$; see Figure 19	[1]			
		$V_{CC} = 1.4 \text{ V to } 4.3 \text{ V}$	-	15	-	MHz
α_{iso}	isolation (OFF-state)	$f_i = 100 \text{ kHz}; R_L = 50 \text{ } \Omega$; see Figure 20	[1]			
		$V_{CC} = 1.4 \text{ V to } 4.3 \text{ V}$	-	-90	-	dB
V_{ct}	crosstalk voltage	between digital inputs and switch; $f_i = 1 \text{ MHz}; C_L = 50 \text{ pF}; R_L = 50 \text{ } \Omega$; see Figure 21				
		$V_{CC} = 1.4 \text{ V to } 3.6 \text{ V}$	-	0.2	-	V
		$V_{CC} = 3.6 \text{ V to } 4.3 \text{ V}$	-	0.3	-	V
Xtalk	crosstalk	between switches; $f_i = 100 \text{ kHz}; R_L = 50 \text{ } \Omega$; see Figure 22	[1]			
		$V_{CC} = 1.4 \text{ V to } 4.3 \text{ V}$	-	-90	-	dB
Q_{inj}	charge injection	$f_i = 1 \text{ MHz}; C_L = 0.1 \text{ nF}; R_L = 1 \text{ M}\Omega; V_{\text{gen}} = 0 \text{ V}; R_{\text{gen}} = 0 \text{ } \Omega$; see Figure 23				
		$V_{CC} = 1.5 \text{ V}$	-	3	-	pC
		$V_{CC} = 1.8 \text{ V}$	-	4	-	pC
		$V_{CC} = 2.5 \text{ V}$	-	6	-	pC
		$V_{CC} = 3.3 \text{ V}$	-	9	-	pC
		$V_{CC} = 4.3 \text{ V}$	-	15	-	pC

[1] f_i is biased at $0.5V_{CC}$.

12.3 Test circuits

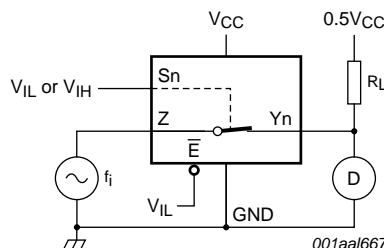
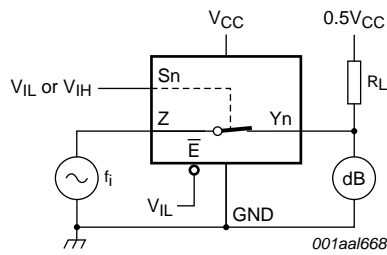
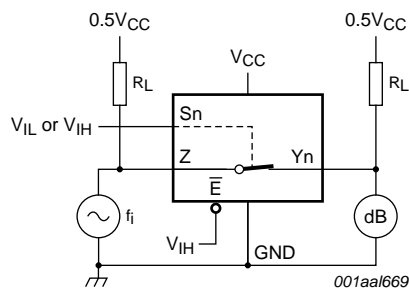


Fig 18. Test circuit for measuring total harmonic distortion



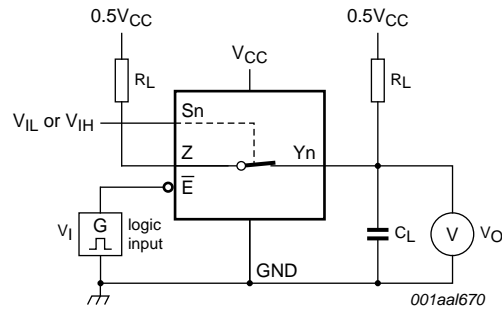
Adjust f_i voltage to obtain 0 dBm level at output. Increase f_i frequency until dB meter reads -3 dB.

Fig 19. Test circuit for measuring the frequency response when channel is in ON-state

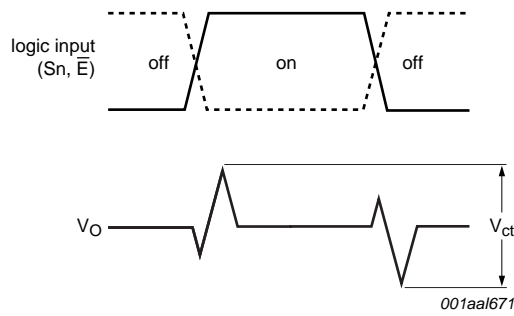


Adjust f_i voltage to obtain 0 dBm level at input.

Fig 20. Test circuit for measuring isolation (OFF-state)



a. Test circuit



b. Input and output pulse definitions

Fig 21. Test circuit for measuring crosstalk voltage between digital inputs and switch

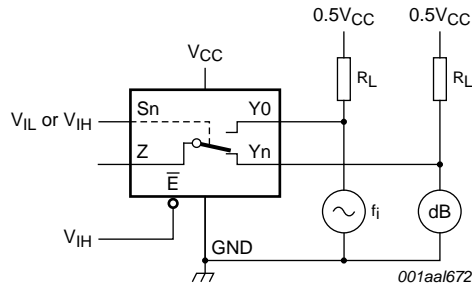
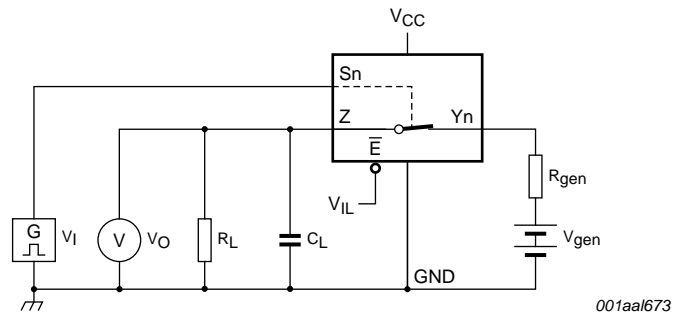
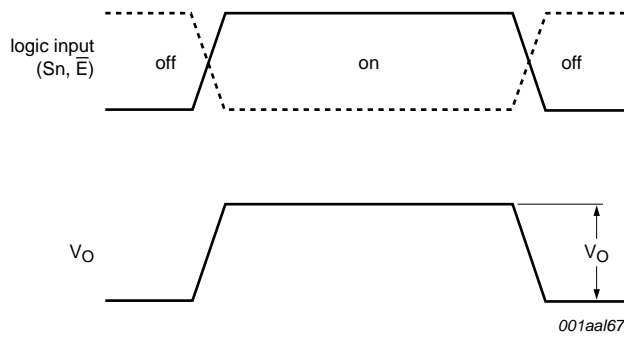


Fig 22. Test circuit for measuring crosstalk between switches



a. Test circuit



b. Input and output pulse definitions

Definition: $Q_{inj} = \Delta V_O \times C_L$.

ΔV_O = output voltage variation.

R_{gen} = generator resistance.

V_{gen} = generator voltage.

V_I may be connected to S_n or \bar{E} .

Fig 23. Test circuit for measuring charge injection

13. Package outline

HXQFN16U: plastic thermal enhanced extremely thin quad flat package; no leads; 16 terminals; UTLP based; body 3 x 3 x 0.5 mm

SOT1039-1

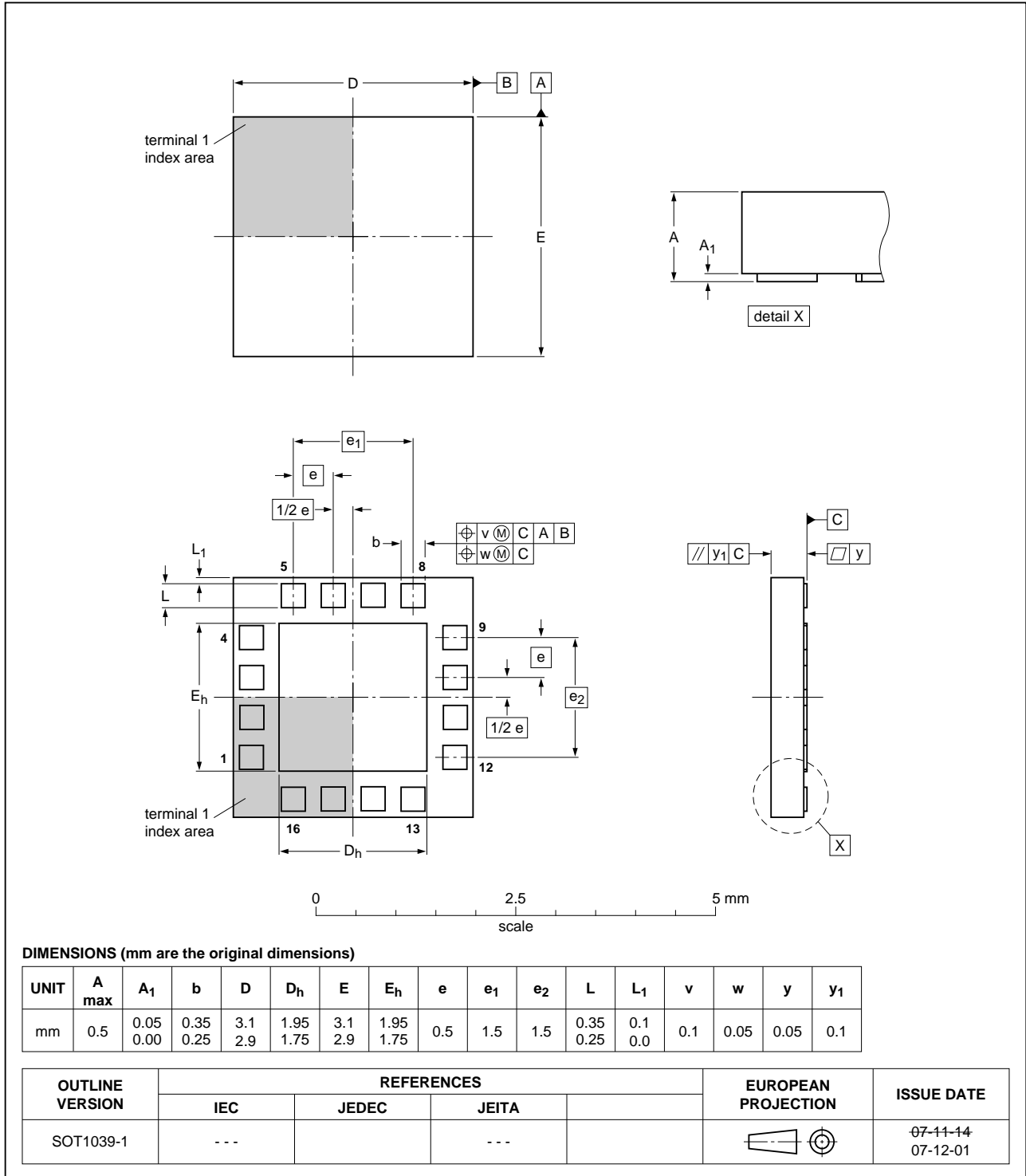


Fig 24. Package outline SOT1039-1 (HXQFN16U)

TSSOP16: plastic thin shrink small outline package; 16 leads; body width 4.4 mm

SOT403-1

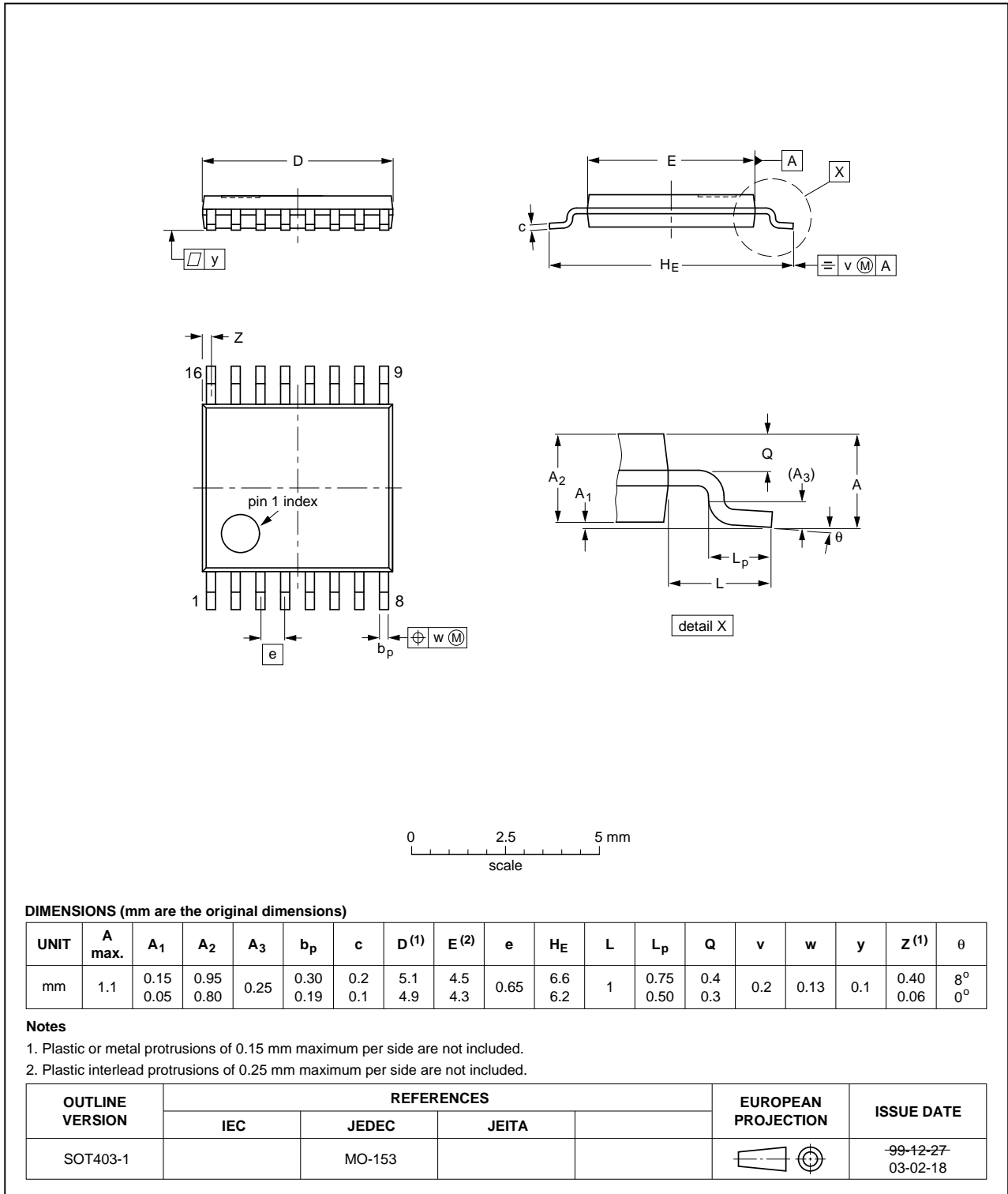


Fig 25. Package outline SOT403-1 (TSSOP16)

14. Abbreviations

Table 13. Abbreviations

Acronym	Description
CDM	Charged Device Model
CMOS	Complementary Metal-Oxide Semiconductor
ESD	ElectroStatic Discharge
HBM	Human Body Model
MM	Machine Model
PDA	Personal Digital Assistant

15. Revision history

Table 14. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
NX3L4051 v.2	20100812	Product data sheet	-	NX3L4051 v.1
Modifications:	• Marking code corrected.			
NX3L4051 v.1	20100415	Product data sheet	-	-

16. Legal information

16.1 Data sheet status

Document status ^{[1][2]}	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

[3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL <http://www.nxp.com>.

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18. Contents

1 General description 1

2 Features and benefits 1

3 Applications 1

4 Ordering information 2

5 Marking 2

6 Functional diagram 3

7 Pinning information 4

7.1 Pinning 4

7.2 Pin description 4

8 Functional description 5

9 Limiting values 5

10 Recommended operating conditions 6

11 Static characteristics 6

11.1 Test circuits 7

11.2 ON resistance 8

11.3 ON resistance test circuit and graphs 9

12 Dynamic characteristics 11

12.1 Waveform and test circuits 12

12.2 Additional dynamic characteristics 14

12.3 Test circuits 14

13 Package outline 18

14 Abbreviations 20

15 Revision history 20

16 Legal information 21

16.1 Data sheet status 21

16.2 Definitions 21

16.3 Disclaimers 21

16.4 Trademarks 22

17 Contact information 22

18 Contents 23

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